

What is claimed is:

1. A substrate treating method for performing a predetermined treatment of substrates as immersed in a treating liquid stored in a treating tank, comprising:
  - a first step of deriving a current treating rate from a relationship between use history and treating rate of the treating liquid and an up-to-date use history of the treating liquid;
  - a second step of determining a corrected treating time by extending a predetermined treating time according to said current treating rate; and
  - a third step of treating the substrates for said corrected treating time.
2. A method as defined in claim 1, wherein said first step is executed by taking into account at least one of a treated number of substrates, a treating rate, a treating time, a substrate type, a rate of over-treatment, a substrate coverage of film and an initial treating rate.
3. A method as defined in claim 1, wherein said first step is executed by taking into account at least one of a treated number of substrates, a treating time and a substrate coverage of film.

4. A method as defined in claim 1, wherein said corrected treating time is derived from;

$$A1 = Ti \cdot (Ri/Rm)$$

where  $Ti$  is an etching time specified in a recipe with reference to a fresh portion of said treating liquid,  $Ri$  is an etching rate of the fresh portion, and  $Rm$  is the current etching rate.

5. A method as defined in claim 2, wherein said corrected treating time is derived from;

$$A1 = Ti \cdot (Ri/Rm)$$

where  $Ti$  is an etching time specified in a recipe with reference to a fresh portion of said treating liquid,  $Ri$  is an etching rate of the fresh portion, and  $Rm$  is the current etching rate.

6. A method as defined in claim 3, wherein said corrected treating time is derived from;

$$A1 = Ti \cdot (Ri/Rm)$$

where  $Ti$  is an etching time specified in a recipe with reference to a fresh portion of said treating liquid,  $Ri$  is an etching rate of the fresh portion, and  $Rm$  is the current etching rate.

7. A method as defined in claim 1, wherein said treating

liquid includes phosphoric acid.

8. A method as defined in claim 2, wherein said treating liquid includes phosphoric acid.

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9. A method as defined in claim 4, wherein said treating liquid includes phosphoric acid.

10. A method as defined in claim 1, wherein said treating liquid includes hydrofluoric acid.

11. A substrate treating apparatus for performing a predetermined treatment of substrates as immersed in a treating liquid stored in a treating tank, comprising:

15 storage means for storing a relationship between use history and treating rate of the treating liquid and an up-to-date use history of the treating liquid;

calculating means for deriving a current treating rate from said relationship between use history and treating rate

20 of the treating liquid and said up-to-date use history of the treating liquid; and

computing means for determining a corrected treating time by extending a predetermined treating time according to said current treating rate;

25 wherein said substrates are treated for said corrected

treating time.

12. A apparatus as defined in claim 11, wherein said  
calculating means is arranged to take into account at least  
5 one of a treated number of substrates, a treating rate, a  
treating time, a substrate type, a rate of over-treatment, a  
substrate coverage of film and an initial treating rate.

13. A apparatus as defined in claim 11, wherein said  
10 calculating means is arranged to take into account at least  
one of a treated number of substrates, a treating time and a  
substrate coverage of film.

14. A apparatus as defined in claim 11, wherein said  
15 calculating means is arranged to derive said corrected treat-  
ing time from;

$$A1 = Ti \cdot (Ri/Rm)$$

where  $Ti$  is an etching time specified in a recipe with refer-  
ence to a fresh portion of said treating liquid,  $Ri$  is an etch-  
20 ing rate of the fresh portion, and  $Rm$  is the current etching  
rate.

15. A apparatus as defined in claim 12, wherein said  
calculating means is arranged to derive said corrected treat-  
25 ing time from;

$$A1 = Ti \cdot (Ri/Rm)$$

where  $Ti$  is an etching time specified in a recipe with reference to a fresh portion of said treating liquid,  $Ri$  is an etching rate of the fresh portion, and  $Rm$  is the current etching rate.

16. A apparatus as defined in claim 13, wherein said calculating means is arranged to derive said corrected treating time from;

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$$A1 = Ti \cdot (Ri/Rm)$$

where  $Ti$  is an etching time specified in a recipe with reference to a fresh portion of said treating liquid,  $Ri$  is an etching rate of the fresh portion, and  $Rm$  is the current etching rate.

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17. A apparatus as defined in claim 11, wherein said treating liquid includes phosphoric acid.

18. A apparatus as defined in claim 12, wherein said treating liquid includes phosphoric acid.

19. A apparatus as defined in claim 14, wherein said treating liquid includes phosphoric acid.

20. A apparatus as defined in claim 11, wherein said treat-

ing liquid includes hydrofluoric acid.